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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	09/296,835
Sheet	1	of	1	Filing Date	April 22, 1999
				First Named Inventor	Ronald A. Weimer
				Art Unit	2813
				Examiner Name	E. Kielin
				Attorney Docket Number	M4065.0319/P319

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (<i>if known</i>)			
EK	A	6,063,698	05/16/00	Tseng et al.	
EL	B	6,197,668	03/06/01	Gardner, et al.	
EK	C	US-2001/0020725	09/13/01	Okuno, et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
Ek	D	LU, et al., "Leakage Current Comparison Between Ultra-Thin Ta ₂ O ₅ films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342			
Ek	E	ALERS, et al., "Intermixing at the Tantalum Oxide/Silicon Interface in Gate Dielectric Structures" Applied Physics Letters 73(11), 14 September 1998, pp. 1517-1519			
Ek	F	LUAN, et al., "Ultra-thin High Quality Ta ₂ O ₅ Dielectric Prepared by In-Situ Rapid Thermal Processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.			

Examiner Signature	<i>En Kielin</i>	Date Considered	6/16/03
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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